Code: AE20 Time: 3 Hours

## Subject: MICROWAVE THEORY & TECHNIQUES

Max. Marks: 100

## **JUNE 2011**

NOTE: There are 9 Questions in all.

- Question 1 is compulsory and carries 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- The answer sheet for the Q.1 will be collected by the invigilator after 45 Minutes of the commencement of the examination.
- Out of the remaining EIGHT Questions answer any FIVE Questions. Each question carries 16 marks.
- Any required data not explicitly given, may be suitably assumed and stated.

## Q.1 Choose the correct or the best alternative in the following:

 $(2 \times 10)$ 

a. The semiconductor diode which can be used in switching circuits at microwave range is

(A) PIN diode	( <b>B</b> ) Varactor diode
(C) Tunnel diode	( <b>D</b> ) Gunn diode

b. Which one of the following modes of transmission will not be supported by a rectangular waveguide?

( <b>A</b> ) TE <sub>10</sub>	<b>(B)</b> TE <sub>11</sub>
(C) $TM_{11}$	<b>(D)</b> $TM_{10}$

c. The skin depth at 1000 MHz, in comparison with that at 500 MHz is

(A) 2	<b>(B)</b>	$\sqrt{2}$
(C) $1/\sqrt{2}$	<b>(D)</b>	1/2

- d. In a TWT, the tube velocity of the axial component of the RF field on the slow-wave structure is kept
  - (A) Equal to the velocity of the electrons.

(C) Pump energy

- (B) Slightly less than the velocity of electrons.
- (C) Slightly more than the velocity of electrons.
- (D) Equal to the velocity of light in free space.
- e. In parametric amplifiers used in microwave communication systems, the amplification is limited by

<b>(A)</b>	Type of biasing	<b>(B)</b> A	A maximum	limit of 10
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**(D)** Frequency of operation

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AMIETE - ET (OLD SCHEME)

f. Which of the following is the correct angular aperture for a paraboloidal reflector antenna for which the aperture number is 0.25?

(A) $45^{\circ}$	<b>(B)</b> 90°
( <b>C</b> ) 120°	<b>(D)</b> 180°

- g. A disadvantage of microstrips with respect to stripline circuits is that the former
  - (A) Do not lend themselves to printed circuits techniques
  - (**B**) Are more likely to radiate
  - (C) Are bulkier
  - (D) Are more expensive and complex to manufacture
- h. Which one of the following is a transferred electron device?

(A) BARITT diode	( <b>B</b> ) IMPATT diode
(C) Gunn diode	( <b>D</b> ) Step recovery diode

i. A 75 ohm transmission line is first short terminated and minima locations are noted. When the short is replaced by a resistive load  $R_L$ , the minima locations are not altered and the VSWR is measured to be 3. What is the value of  $R_L$ ?

(A) 25 ohms	<b>(B)</b>	50 ohms
( <b>C</b> ) 225 ohms	<b>(D)</b>	250 ohms

- j. In microwave power measurement using bolometers the principle of working is the variation of
  - (A) Inductance with absorption of power
  - (**B**) Resistance with absorption of power
  - (C) Capacitance with absorption of power
  - (D) Cavity dimensions with heat generated by the power

## Answer any FIVE Questions out of EIGHT Questions. Each question carries 16 marks.

the outer conductor is 6 mm 1.60. Calculate the character	n and the dielectric constant of the insuristic impedance. If the nominal capac	lation is
matrix for the same. (i) Directivity	(ii) Coupling factor (iv) Isolation.	write S
	<ul> <li>the outer conductor is 6 mn 1.60. Calculate the character 60 pF/m. Find the value of</li> <li>Define the following terms matrix for the same.</li> </ul>	(i) Directivity (ii) Coupling factor

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	a 10 GHz carrier from a coaxial	$TE_{10}$ modes. This waveguide is fed by cable. If $TE_{10}$ wave is propagated, n (ii) guide wavelength (iii) phase and	(8)
Q.4	a. Explain the operation of a Faraday sketch. List the applications of Ferrit	-	(8)
	b. Derive an expression for resonant resonator.		(8)
Q.5	spacing in either cavity $d=1$ mm, sp cm, effective shunt impedance $R_{sh}=4$	I <sub>0</sub> =30 mA, Frequency F=8 GHz, gap acing between centres of cavities L= 4 $40 \text{ k}\Omega$ . Determine: me of electrons. (iii) input voltage for	(8)
	b. Explain how amplification is achieve	ed in a magnetron with neat sketch. (8	6)
Q.6	a. Obtain the scattering matrix of H pla	nne Tee. (8	(8)
	b. Differentiate amongst TE, TM, TEM	1 & HE waves. (4	(4)
	c. Enumerate the advantages and disad	vantages of MICS. (4	(4)
Q.7	a. Describe the method for micro measurement.	- ·	(8)
	b. Explain working of TWT with neat s	sketch. (i	(8)
Q.8	a. Explain in detail the operation of Gu	nn diode with neat sketch. (8	(8)
	b. Derive the radar range equation. maximum range of RADAR.	*	(8)
Q.9	Write short notes on any TWO of th	e following:	
	<ul> <li>(i) Measurement of high VSWR</li> <li>(ii) Microwave antennas</li> <li>(iii) Reflex Klystron</li> <li>(iv) Impedance matching in RF Transition</li> </ul>	ansmission line. (2×8	8)